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BTA412Y-600B

3Q Hi-Com Triac

10 June 2014

Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT78D (TO-220AB) internally insulated plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series B" triac will commute the full RMS current at the maximum rated junction temperature without the aid of a snubber. This device has high T_j operating capability and an internally isolated mounting base.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High surge capability
- High $T_{j(max)}$
- Isolated mounting base with 2500 V (RMS) isolation
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- Electronic thermostats (heating and cooling)
- High power motor controls
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------|--------------------------------------|--|-----|-----|-----|--------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 600 | V |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | - | 140 | A |
| T_j | junction temperature | | - | - | 150 | $^{\circ}\text{C}$ |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{mb} \leq 116\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | - | 12 | A |



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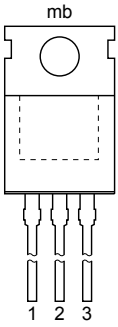

BTA412Y-600B

3Q Hi-Com Triac

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|----------------------|--|-----|-----|-----|------|
| Static characteristics | | | | | | |
| I _{GT} | gate trigger current | V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7 | 2 | - | 50 | mA |
| | | V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7 | 2 | - | 50 | mA |
| | | V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7 | 2 | - | 50 | mA |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|---|--|
| 1 | T1 | main terminal 1 |  <p>TO-220AB (SOT78D)</p> |  <p>sym051</p> |
| 2 | T2 | main terminal 2 | | |
| 3 | G | gate | | |
| mb | n.c. | mounting base; isolated | | |

6. Ordering information

Table 3. Ordering information

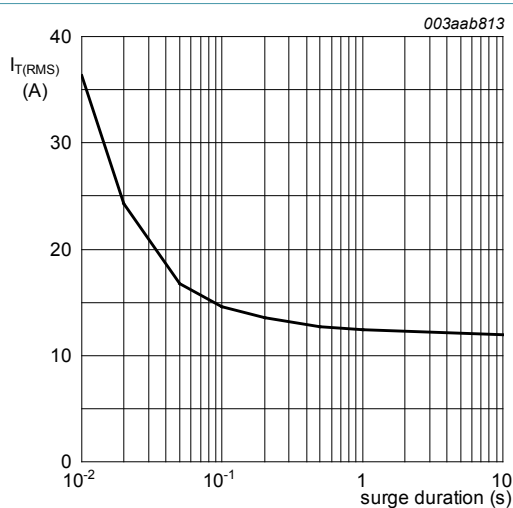
| Type number | Package | | |
|--------------|----------|---|---------|
| | Name | Description | Version |
| BTA412Y-600B | TO-220AB | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 | SOT78D |

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------|--------------------------------------|--|-----|-----|-------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 600 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{mb} \leq 116\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | 12 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | 140 | A |
| | | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$ | - | 153 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ ms}$; SIN | - | 98 | A^2s |
| di_T/dt | rate of rise of on-state current | $I_T = 20\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu s$ | - | 100 | $A/\mu s$ |
| I_{GM} | peak gate current | | - | 2 | A |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| T_{stg} | storage temperature | | -40 | 150 | $^{\circ}C$ |
| T_j | junction temperature | | - | 150 | $^{\circ}C$ |



$f = 50\text{ Hz}$; $T_{mb} = 116\text{ °C}$

Fig. 1. RMS on-state current as a function of surge duration; maximum values

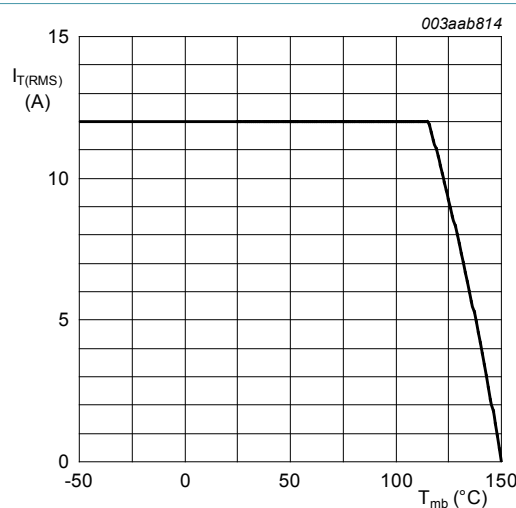


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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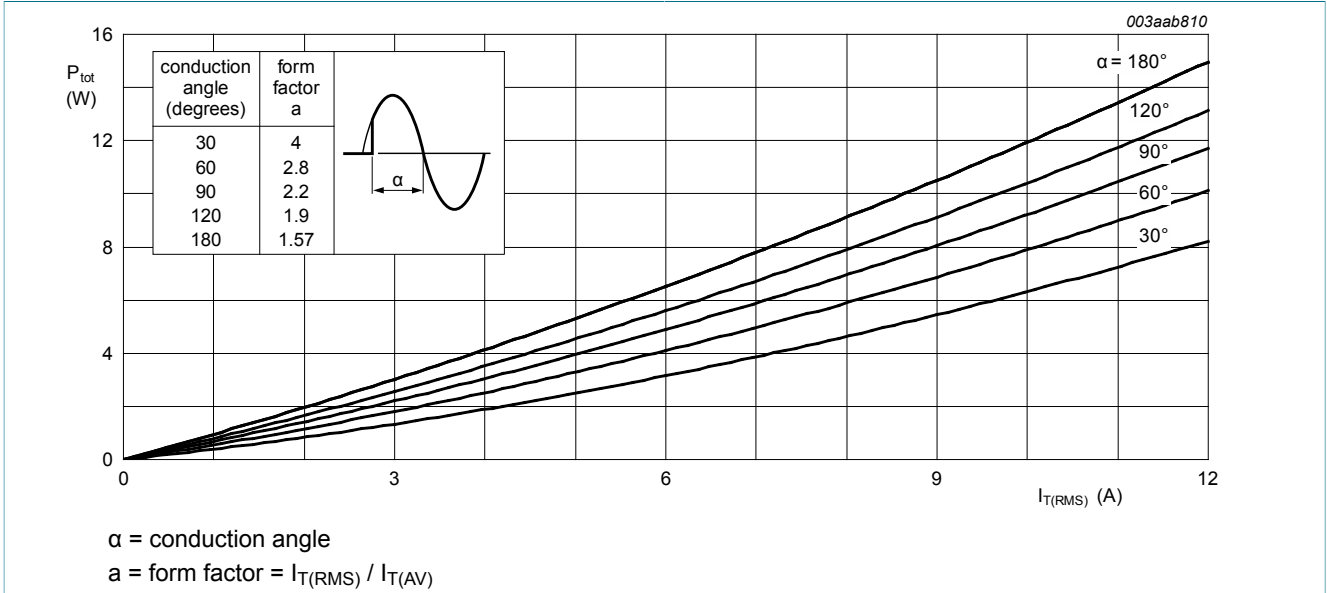


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

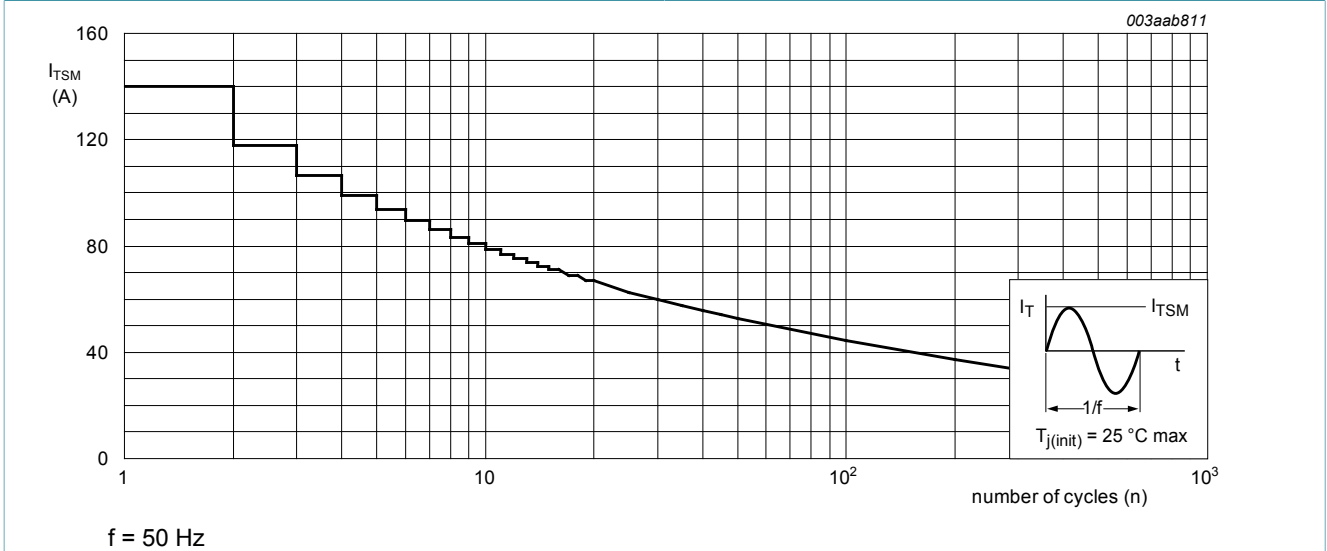
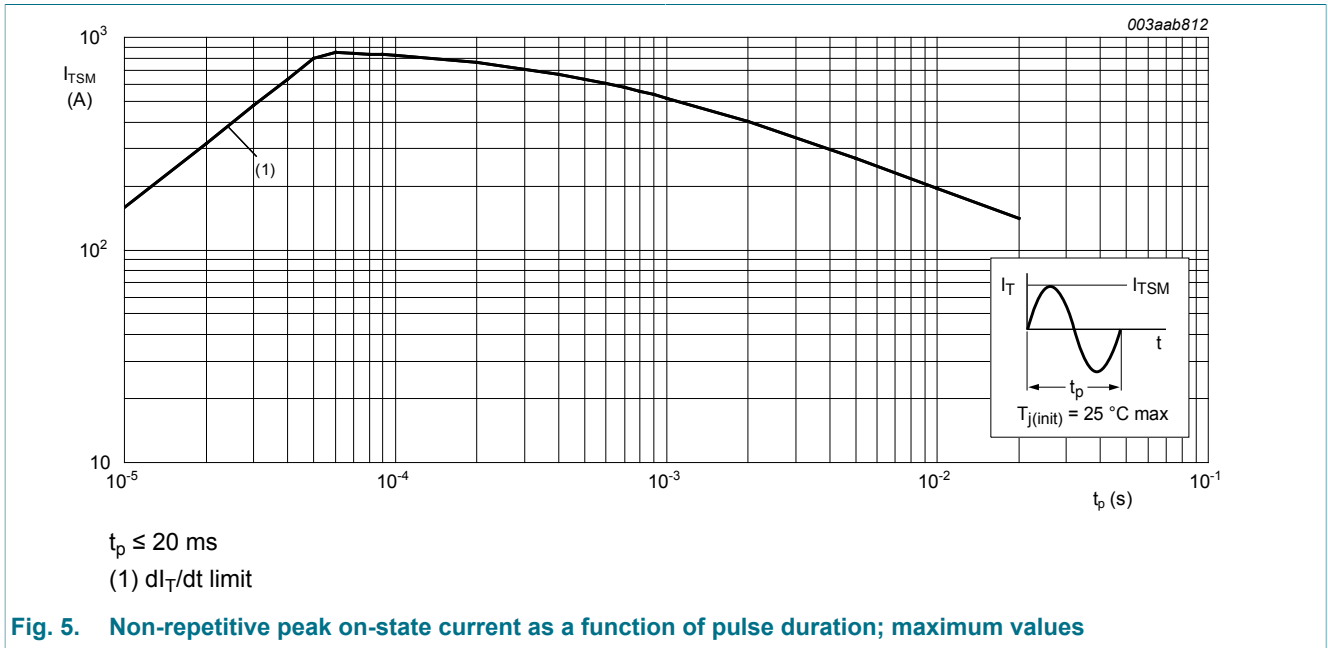


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; Fig. 6 | - | - | 2.1 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |

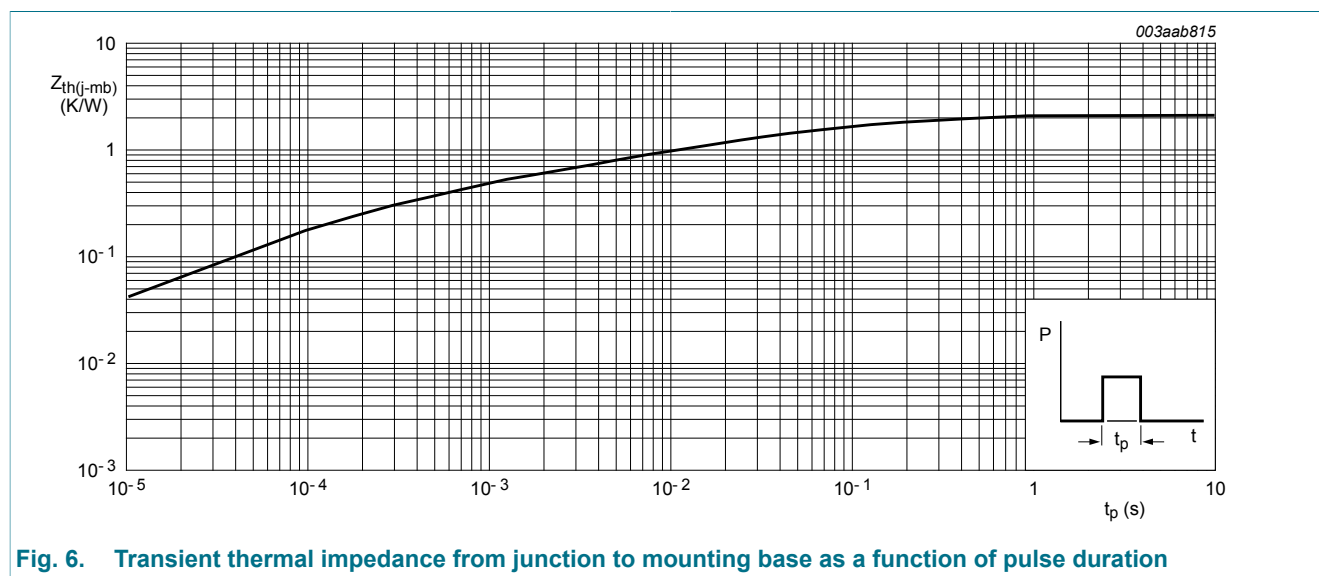


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Isolation characteristics

Table 6. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------|-----------------------|---|-----|-----|------|------|
| $V_{isol(RMS)}$ | RMS isolation voltage | from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$; $RH \leq 65\%$; $T_{mb} = 25\text{ }^\circ\text{C}$ | - | - | 2500 | V |
| C_{isol} | isolation capacitance | from main terminal 2 to external heatsink; $f = 1\text{ MHz}$; $T_{mb} = 25\text{ }^\circ\text{C}$ | - | 10 | - | pF |

10. Characteristics

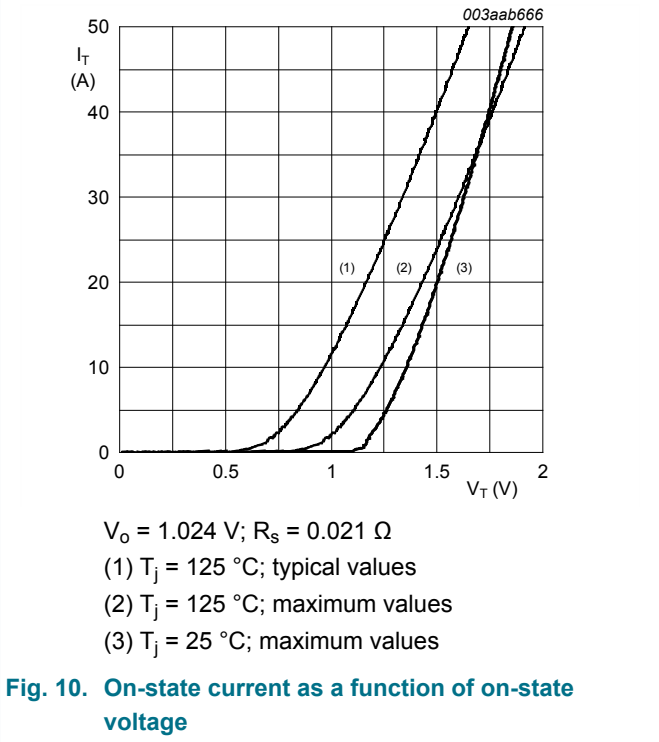
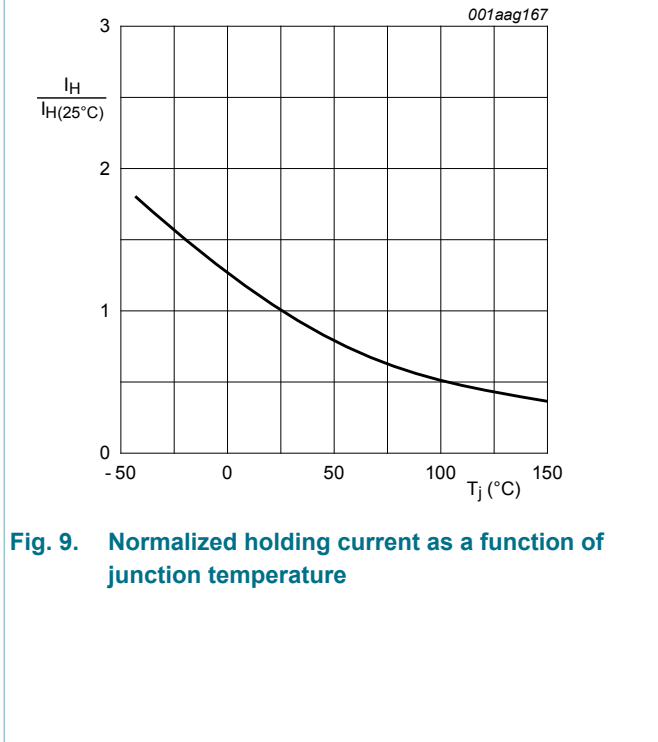
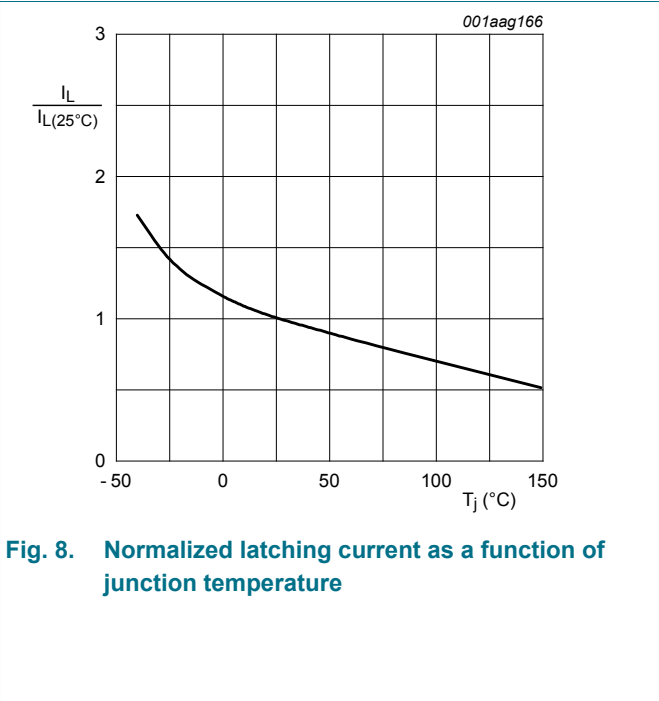
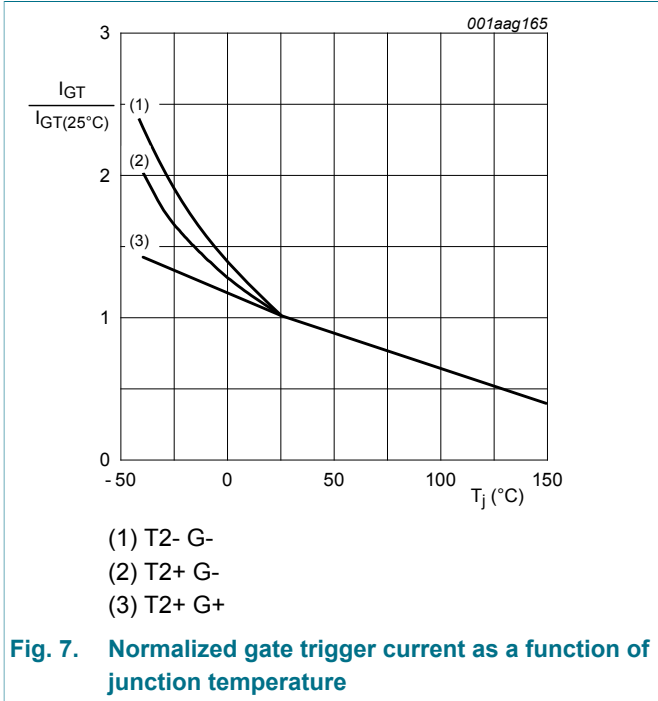
Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|---|------|-----|-----|------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7 | 2 | - | 50 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7 | 2 | - | 50 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7 | 2 | - | 50 | mA |
| I_L | latching current | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 8 | - | - | 60 | mA |
| | | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 8 | - | - | 90 | mA |
| | | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 8 | - | - | 60 | mA |
| I_H | holding current | $V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9 | - | - | 60 | mA |
| V_T | on-state voltage | $I_T = 18\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10 | - | 1.3 | 1.5 | V |
| V_{GT} | gate trigger voltage | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11 | - | 0.8 | 1 | V |
| | | $V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 150\text{ °C}$; Fig. 11 | 0.25 | 0.4 | - | V |
| I_D | off-state current | $V_D = 600\text{ V}$; $T_j = 125\text{ °C}$ | - | 0.1 | 0.5 | mA |
| | | $V_D = 600\text{ V}$; $T_j = 150\text{ °C}$ | - | 0.4 | 2 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 402\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 1000 | - | - | V/ μ s |
| | | $V_{DM} = 402\text{ V}$; $T_j = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 600 | - | - | V/ μ s |
| dI_{com}/dt | rate of change of commutating current | $V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 12\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit | 20 | - | - | A/ms |
| | | $V_D = 400\text{ V}$; $T_j = 150\text{ °C}$; $I_{T(RMS)} = 12\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit | 8 | - | - | A/ms |

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3Q Hi-Com Triac



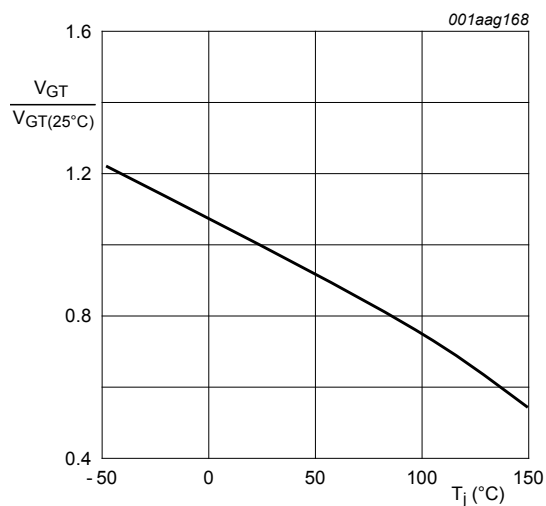


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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11. Package outline

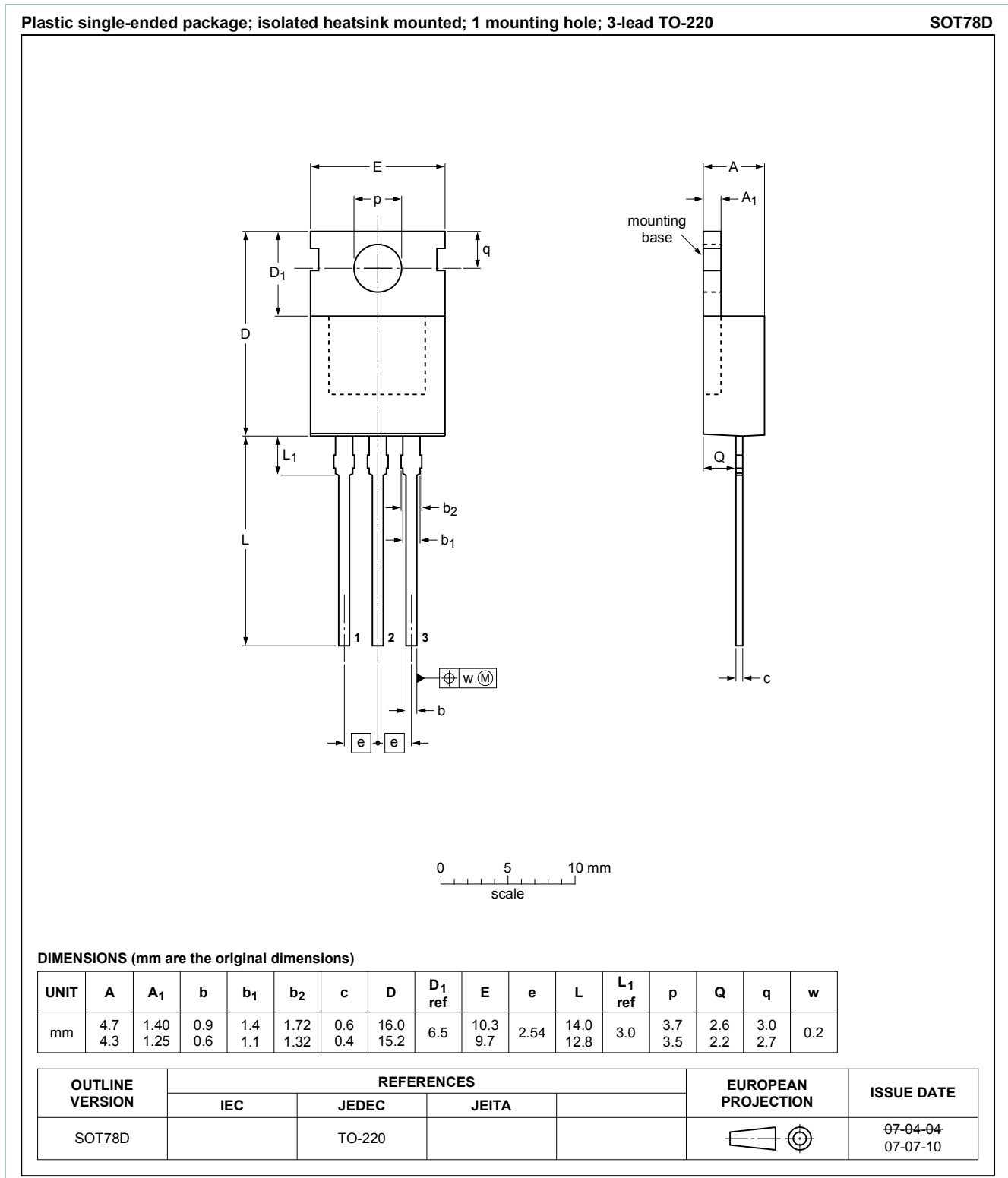


Fig. 12. Package outline TO-220AB (SOT78D)

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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13. Contents

| | | |
|------|---------------------------------|----|
| 1 | General description | 1 |
| 2 | Features and benefits | 1 |
| 3 | Applications | 1 |
| 4 | Quick reference data | 1 |
| 5 | Pinning information | 2 |
| 6 | Ordering information | 2 |
| 7 | Limiting values | 3 |
| 8 | Thermal characteristics | 6 |
| 9 | Isolation characteristics | 6 |
| 10 | Characteristics | 7 |
| 11 | Package outline | 10 |
| 12 | Legal information | 11 |
| 12.1 | Data sheet status | 11 |
| 12.2 | Definitions | 11 |
| 12.3 | Disclaimers | 11 |
| 12.4 | Trademarks | 12 |

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